

**FH102**

High-Frequency Low-Noise Amp, Differential Amp Applications

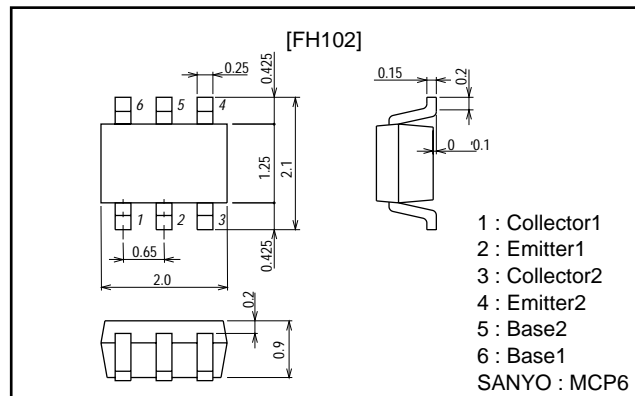
Features

- Composite type with 2 transistors contained in the MCP package currently in use, improving the mounting efficiency greatly.
- The FH102 is formed with two chips, being equivalent to the 2SC5226, placed in one package.
- Optimal for differential amplification due to excellent thermal equilibrium and pair capability.

Package Dimensions

unit: mm

2149-MCP6



Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		20	V
Collector-to-Emitter Voltage	V_{CEO}		10	V
Emitter-to-Base Voltage	V_{EBO}		2	V
Collector Current	I_C		70	mA
Collector Dissipation	P_C	Mounted on ceramic board (250mm ² ×0.8mm), 1unit	300	mW
Total Dissipation	P_T	Mounted on ceramic board (250mm ² ×0.8mm)	500	mW
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=10\text{V}, I_E=0$			1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=1\text{V}, I_C=0$			10	μA
DC Current Gain	h_{FE}	$V_{CE}=5\text{V}, I_C=20\text{mA}$	90		200	
DC Current Gain Ratio	$h_{FE}(\text{small/large})$	$V_{CE}=5\text{V}, I_C=20\text{mA}$	0.7	0.95		
Base-to-Emitter Voltage Difference	$V_{BE}(\text{small-large})$	$V_{CE}=5\text{V}, I_C=20\text{mA}$		1.0		mV
Gain-Bandwidth Product	f_T	$V_{CE}=5\text{V}, I_C=20\text{mA}$	5	7		GHz
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$		0.75	1.2	pF
Reverse Transfer Capacitance	C_{re}	$V_{CB}=10\text{V}, f=1\text{MHz}$		0.5		pF

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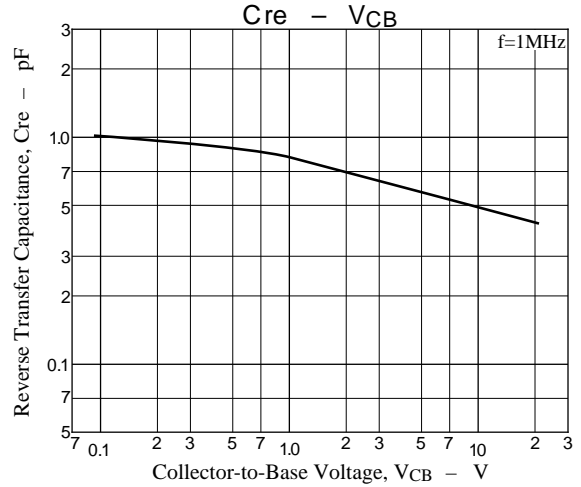
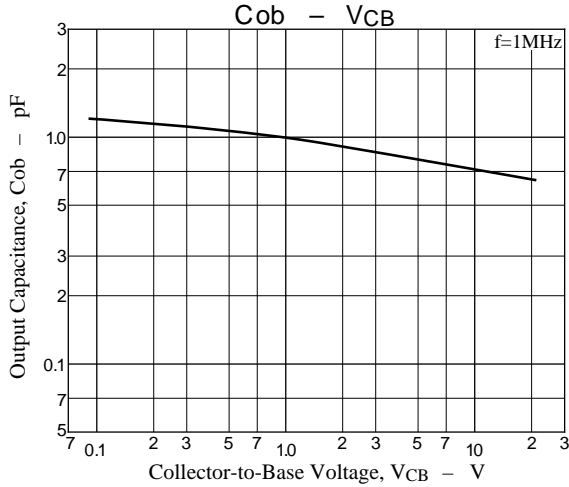
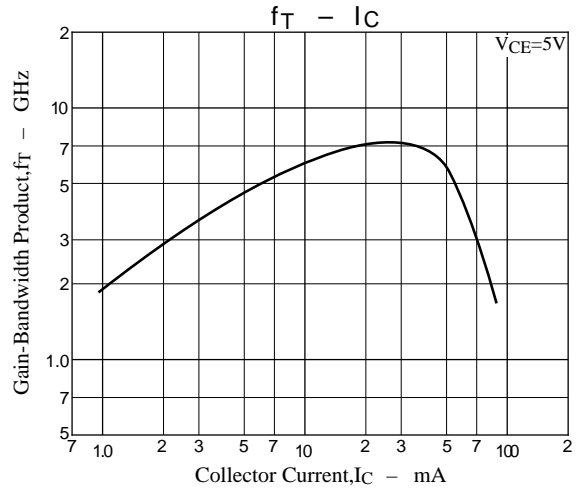
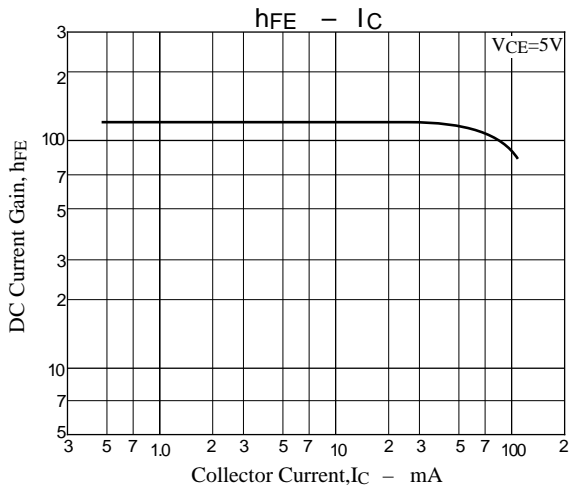
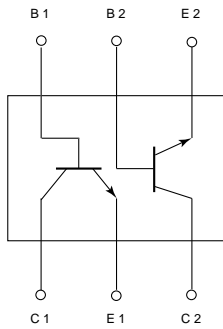
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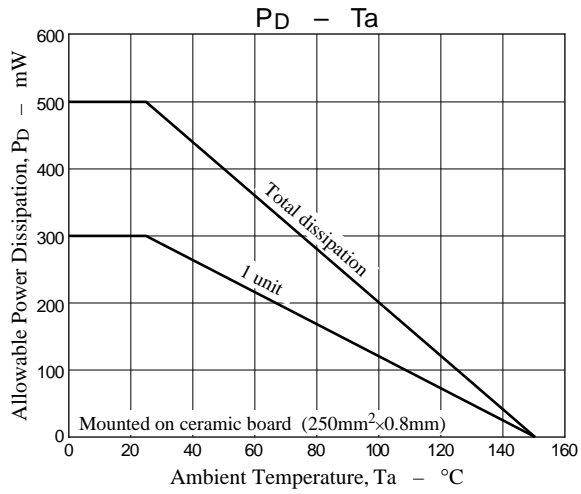
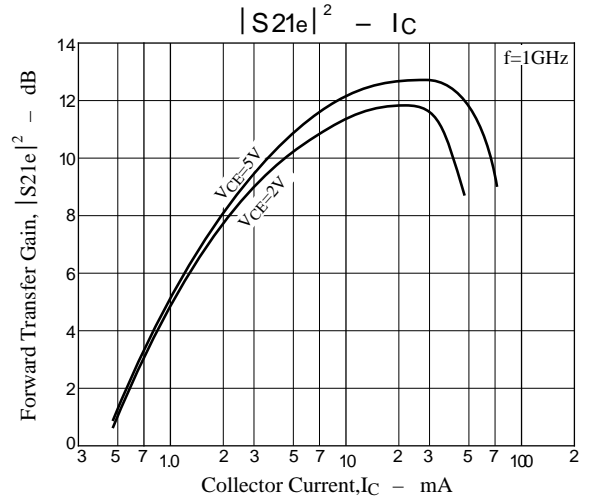
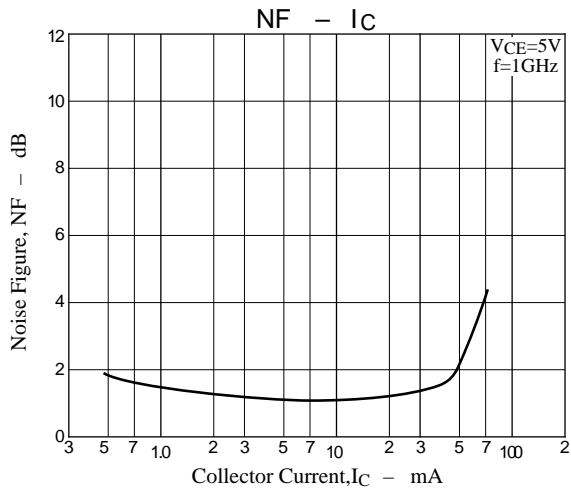
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Transfer Gain	$ S_{21e} ^2(1)$	$V_{CE}=5V, I_C=20mA, f=1GHz$	9	12		dB
	$ S_{21e} ^2(2)$	$V_{CE}=5V, I_C=3mA, f=1GHz$		8		dB
Noise Figure	NF	$V_{CE}=5V, I_C=7mA, f=1GHz$		1.0	1.8	dB

Note) The specifications shown above are for each individual transistor except the h_{FE} (small/large) and V_{BE} (small-large) for which pair capability is also shown.

Marking : 102

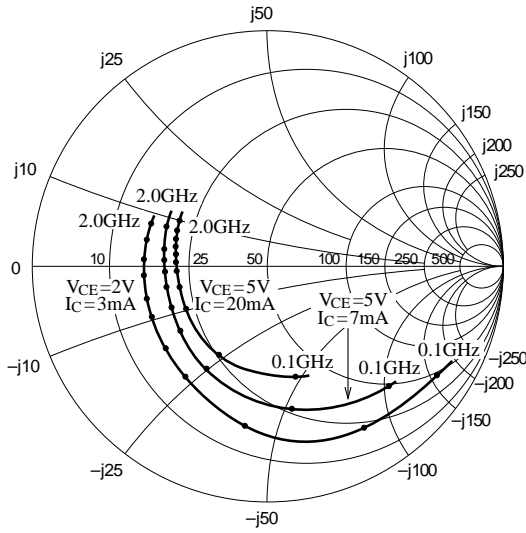
Electrical Connection



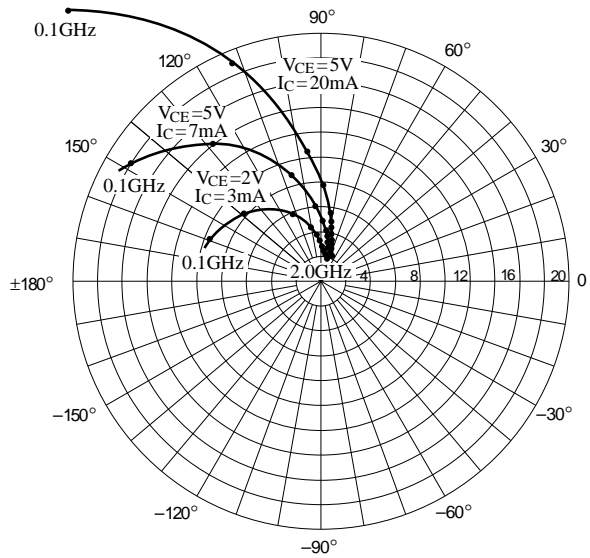


S Parameters

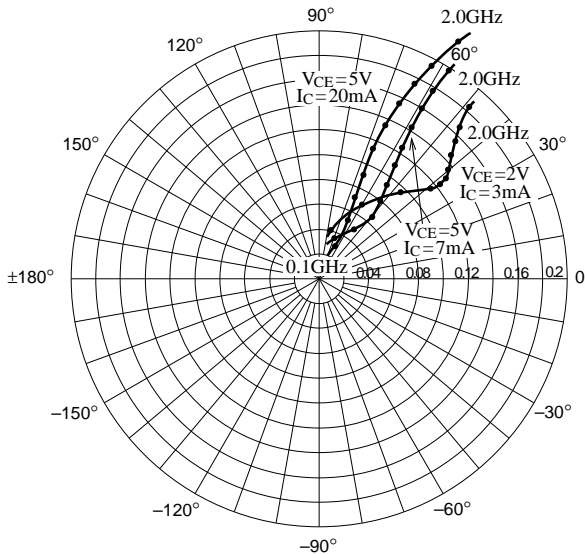
f=100MHz, 200 to 2000MHz (200MHz step)



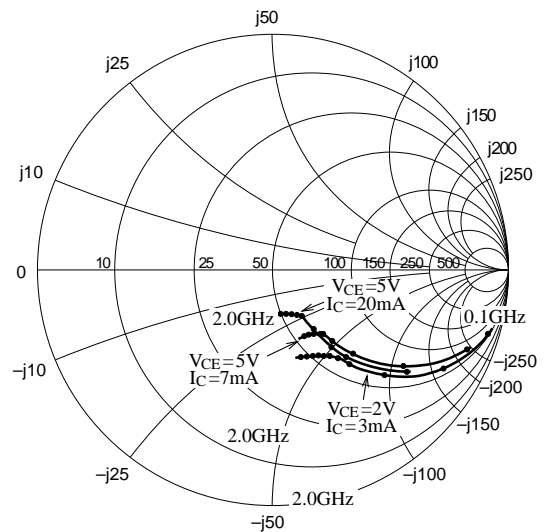
f=100MHz, 200 to 2000MHz (200MHz step)



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FH102

S Parameters (Common emitter)

$V_{CE}=5V, I_C=7mA, Z_O=50\Omega$

Freq(MHz)	S ₁₁	∠ S ₁₁	S ₂₁	∠ S ₂₁	S ₁₂	∠ S ₁₂	S ₂₂	∠ S ₂₂
100	0.720	-46.0	17.973	148.5	0.030	68.5	0.880	-23.6
200	0.612	-80.9	13.927	127.3	0.047	57.1	0.697	-37.6
400	0.497	-121.3	8.656	105.0	0.066	51.3	0.479	-47.6
600	0.456	-143.5	6.080	92.8	0.079	52.9	0.382	-50.5
800	0.440	-157.6	4.725	84.3	0.094	55.4	0.339	-51.8
1000	0.436	-167.5	3.864	77.0	0.110	56.8	0.323	-53.4
1200	0.434	-176.1	3.258	70.3	0.126	57.9	0.312	-55.8
1400	0.433	176.6	2.847	64.5	0.143	58.4	0.304	-58.3
1600	0.433	170.9	2.329	57.4	0.160	58.9	0.296	-62.0
1800	0.434	165.0	2.252	54.2	0.178	58.6	0.293	-65.0
2000	0.439	159.6	2.057	49.2	0.197	58.1	0.294	-68.1

$V_{CE}=5V, I_C=20mA, Z_O=50\Omega$

Freq(MHz)	S ₁₁	∠ S ₁₁	S ₂₁	∠ S ₂₁	S ₁₂	∠ S ₁₂	S ₂₂	∠ S ₂₂
100	0.481	-78.8	29.795	132.9	0.022	63.9	0.707	-38.2
200	0.420	-119.2	19.008	112.2	0.033	60.8	0.470	-51.1
400	0.391	-151.6	10.416	95.4	0.052	64.7	0.296	-55.3
600	0.386	-166.4	7.084	86.6	0.071	67.2	0.236	-56.1
800	0.381	-175.9	5.407	80.1	0.092	68.4	0.213	-56.6
1000	0.382	178.2	4.401	74.1	0.114	67.8	0.208	-57.9
1200	0.385	172.1	3.701	68.5	0.134	66.8	0.204	-60.7
1400	0.388	166.7	3.217	63.6	0.156	65.6	0.202	-63.5
1600	0.390	162.1	2.839	58.8	0.176	64.0	0.199	-67.9
1800	0.391	156.7	2.534	54.3	0.197	62.4	0.197	-71.2
2000	0.394	152.1	2.319	50.1	0.219	60.6	0.197	-74.2

$V_{CE}=2V, I_C=3mA, Z_O=50\Omega$

Freq(MHz)	S ₁₁	∠ S ₁₁	S ₂₁	∠ S ₂₁	S ₁₂	∠ S ₁₂	S ₂₂	∠ S ₂₂
100	0.858	-32.4	9.413	157.2	0.040	72.6	0.945	-16.5
200	0.782	-60.7	8.187	138.5	0.070	59.2	0.833	-29.3
400	0.653	-101.1	5.855	113.8	0.101	44.5	0.637	-43.2
600	0.588	-126.5	4.337	98.4	0.114	39.1	0.515	-50.0
800	0.557	-143.7	3.444	87.7	0.122	38.0	0.454	-53.8
1000	0.543	-156.3	2.871	78.5	0.130	38.6	0.426	-57.1
1200	0.536	-166.8	2.446	70.5	0.137	40.3	0.407	-60.3
1400	0.533	-175.5	2.145	63.5	0.146	42.5	0.393	-63.8
1600	0.527	177.0	1.904	57.1	0.155	45.0	0.382	-68.0
1800	0.525	170.3	1.714	51.7	0.168	47.3	0.379	-72.0
2000	0.528	163.8	1.564	45.9	0.183	49.2	0.378	-75.8